chanhvinh.com

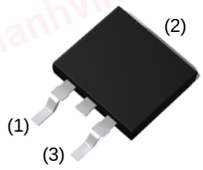
RGT20NL65

650V 10A Field Stop Trench IGBT Datasheet

V_{CES}	650V
$I_{C\ (100°C)}$	10A
$V_{CE(sat)\ (Typ.)}$	1.65V
P_D	106W

●Outline

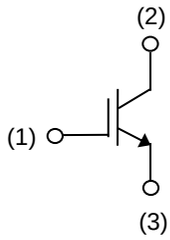
LPDL (TO-263L)



●Features

1) Low Collector - Emitter Saturation Voltage
2) Low Switching Loss
3) Short Circuit Withstand Time 5μs
4) Pb - free Lead Plating ; RoHS Compliant

●Inner Circuit



(1) Gate
(2) Collector
(3) Emitter

●Application

General Inverter
UPS
Power Conditioner
Welder

●Packaging Specifications

Type	Packaging	Taping
	Reel Size (mm)	330
	Tape Width (mm)	24
	Basic Ordering Unit (pcs)	1,000
	Packing Code	TL
	Marking	RGT20NL65

●Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T_C = 25°C	I_C	20	A
	T_C = 100°C	I_C	10	A
Pulsed Collector Current		I_{CP} *1	30	A
Power Dissipation	T_C = 25°C	P_D	106	W
	T_C = 100°C	P_D	53	W
Operating Junction Temperature		T_j	-40 to +175	°C
Storage Temperature		T_{stg}	-55 to +175	°C

*1 Pulse width limited by $T_{jmax.}$

© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.41	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	BV_{CES}	I_C = 10μA, V_{GE} = 0V	650	-	-	V
Collector Cut - off Current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I_{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V_{CE} = 5V, I_C = 6.7mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10A, V_{GE} = 15V,				V
		T_j = 25°C	-	1.65	2.1	
		T_j = 175°C	-	2.15	-	

© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●**IGBT Electrical Characteristics** (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{ies}	V_{CE} = 30V,	-	610	-	pF
Output Capacitance	C_{oes}	V_{GE} = 0V,	-	25	-	
Reverse transfer Capacitance	C_{res}	f = 1MHz	-	9	-	
Total Gate Charge	Q_g	V_{CE} = 300V,	-	22	-	nC
Gate - Emitter Charge	Q_{ge}	I_C = 10A,	-	6	-	
Gate - Collector Charge	Q_{gc}	V_{GE} = 15V	-	9	-	
Turn - on Delay Time	$t_{d(on)}$	I_C = 10A, V_{CC} = 400V, V_{GE} = 15V, R_G = 10Ω, T_j = 25°C Inductive Load	-	12	-	ns
Rise Time	t_r		-	18	-	
Turn - off Delay Time	$t_{d(off)}$		-	32	-	
Fall Time	t_f		-	104	-	
Turn - on Delay Time	$t_{d(on)}$	I_C = 10A, V_{CC} = 400V, V_{GE} = 15V, R_G = 10Ω, T_j = 175°C Inductive Load	-	13	-	ns
Rise Time	t_r		-	18	-	
Turn - off Delay Time	$t_{d(off)}$		-	34	-	
Fall Time	t_f		-	140	-	
Reverse Bias Safe Operating Area	RBSOA	I_C = 30A, V_{CC} = 520V, V_P = 650V, V_{GE} = 15V, R_G = 50Ω, T_j = 175℃	FULL SQUARE			-
Short Circuit Withstand Time	t_{sc}	V_{CC} ≦ 360V, V_{GE} = 15V, T_j = 25℃	5	-	-	μs

© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

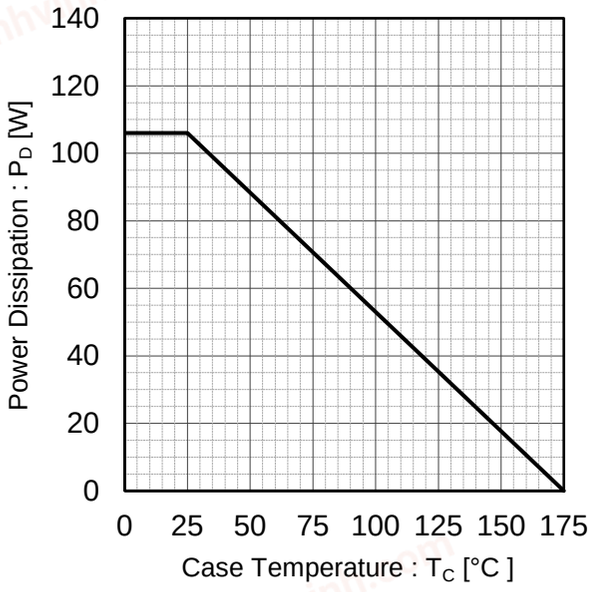


Fig.2 Collector Current vs. Case Temperature

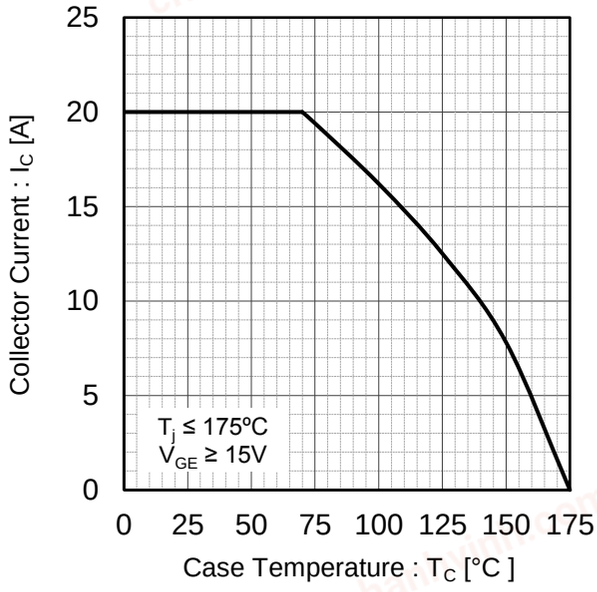


Fig.3 Forward Bias Safe Operating Area

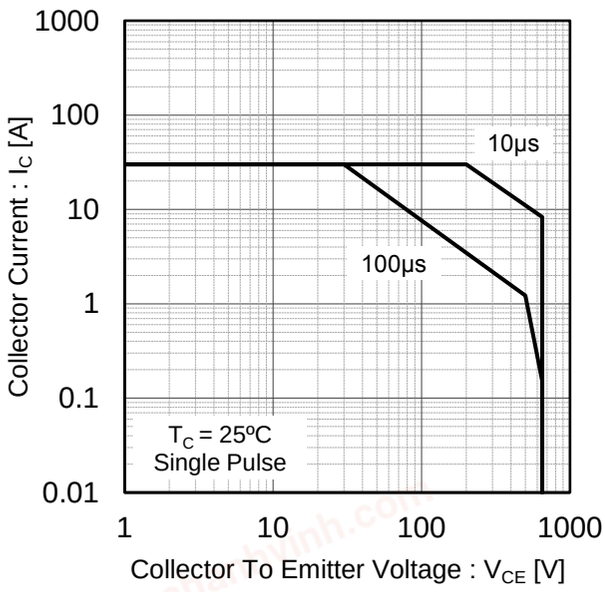
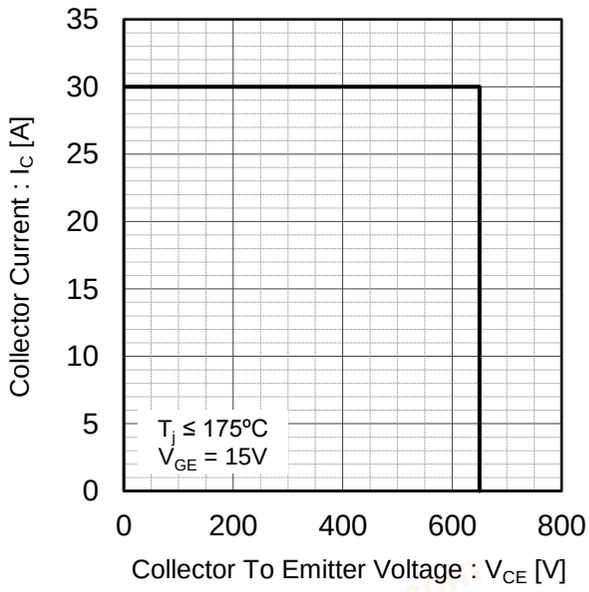


Fig.4 Reverse Bias Safe Operating Area



© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

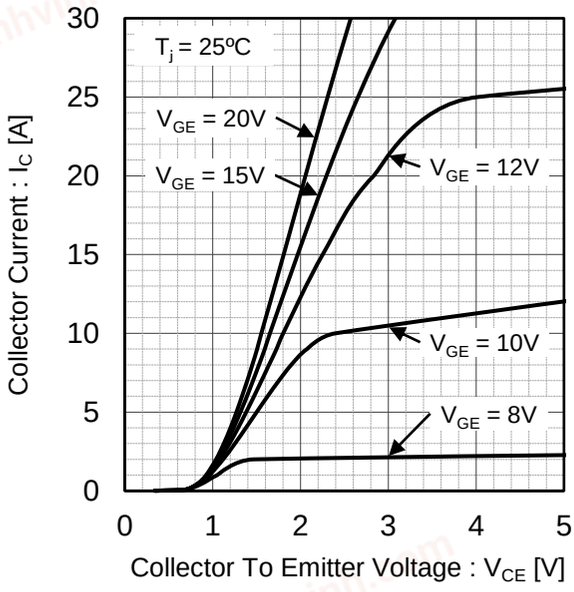


Fig.6 Typical Output Characteristics

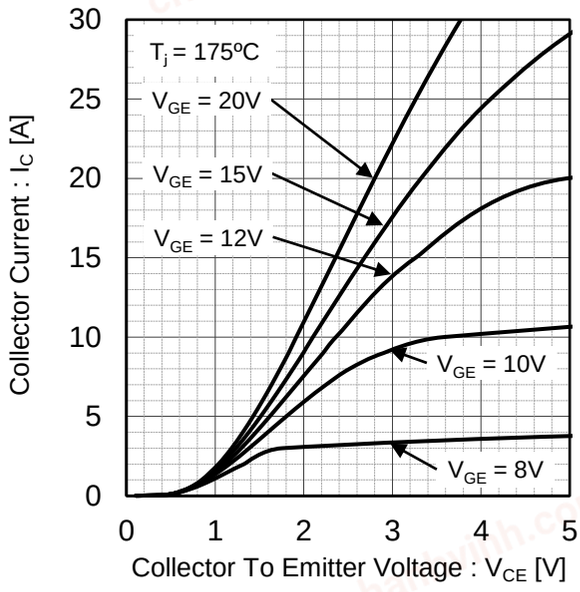


Fig.7 Typical Transfer Characteristics

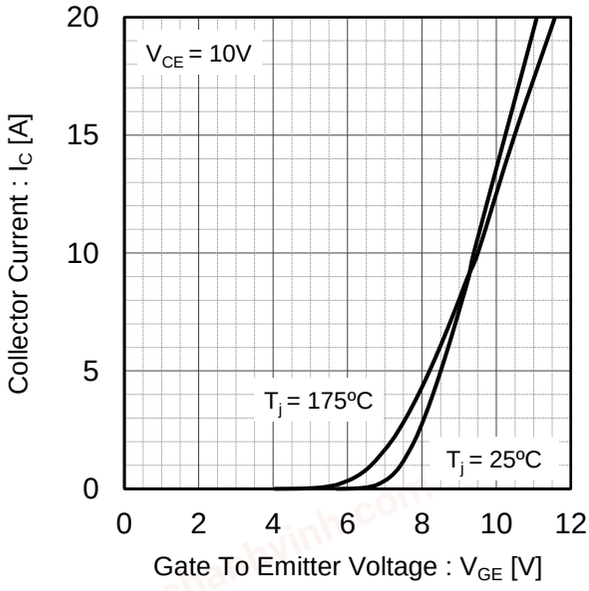
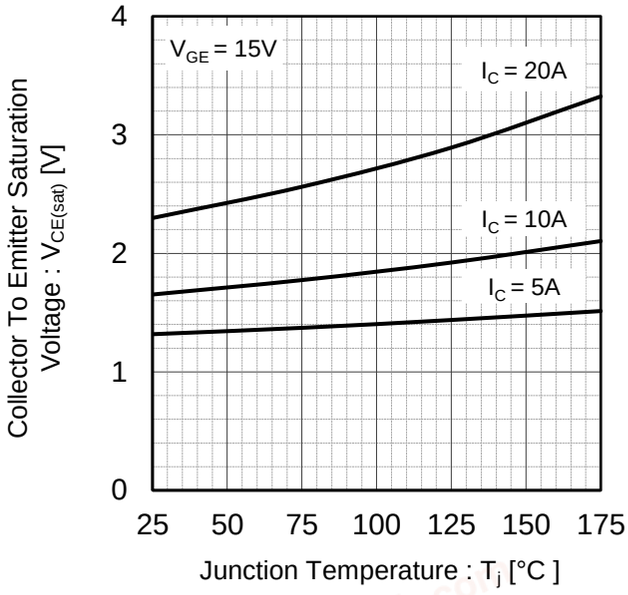


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

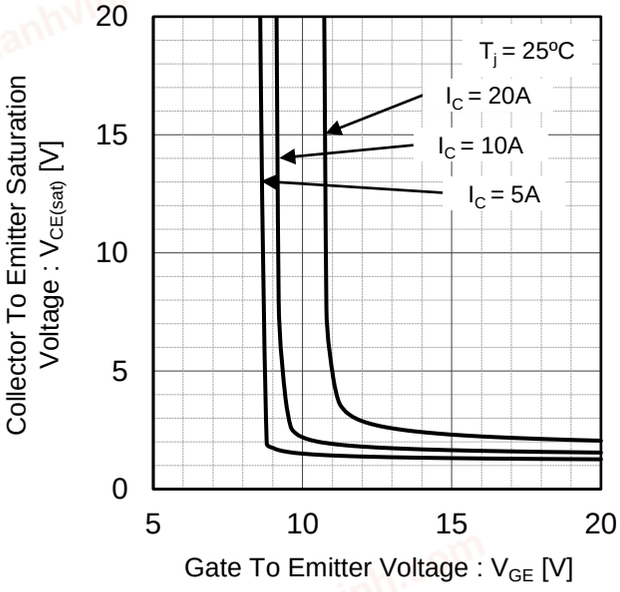


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

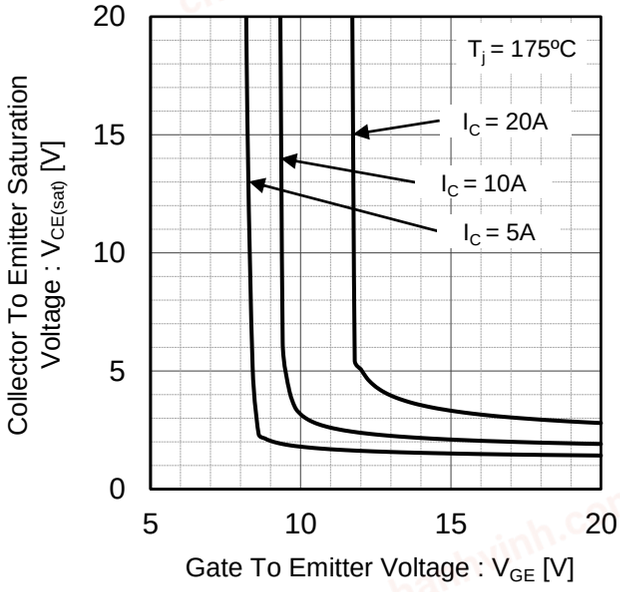


Fig.11 Typical Switching Time vs. Collector Current

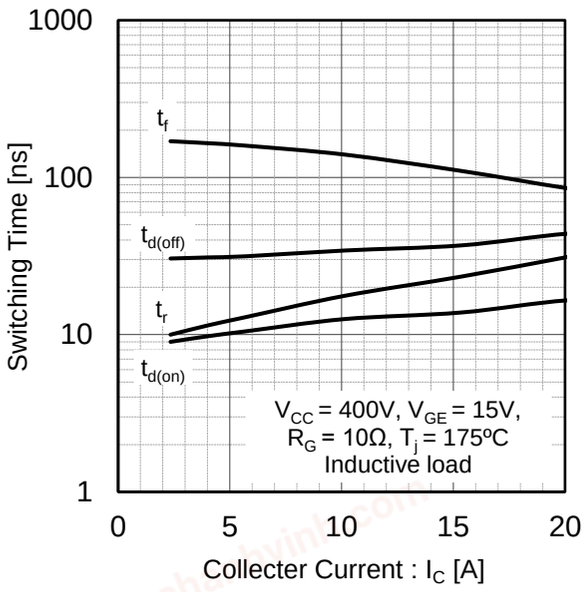
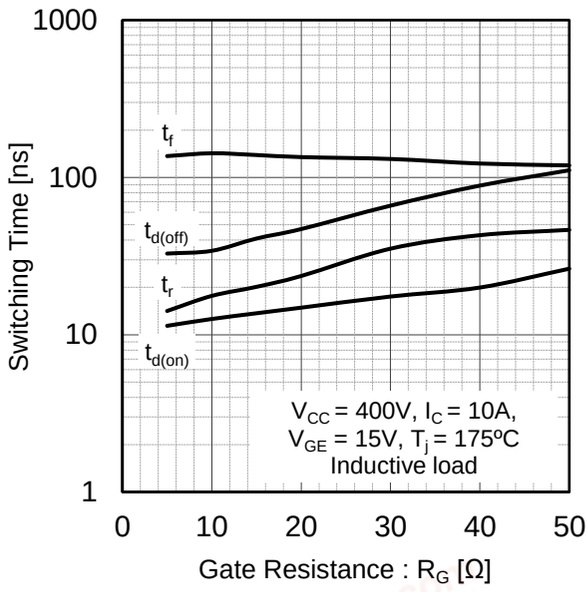


Fig.12 Typical Switching Time vs. Gate Resistance



© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

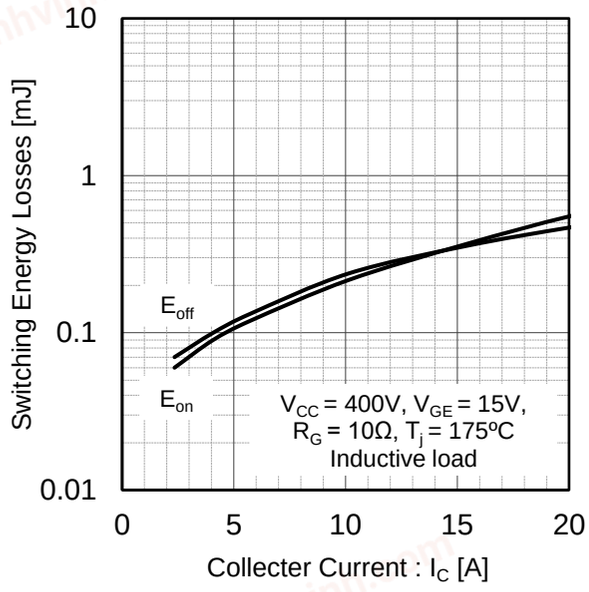


Fig.14 Typocal Switching Energy Losses vs. Gate Resistance

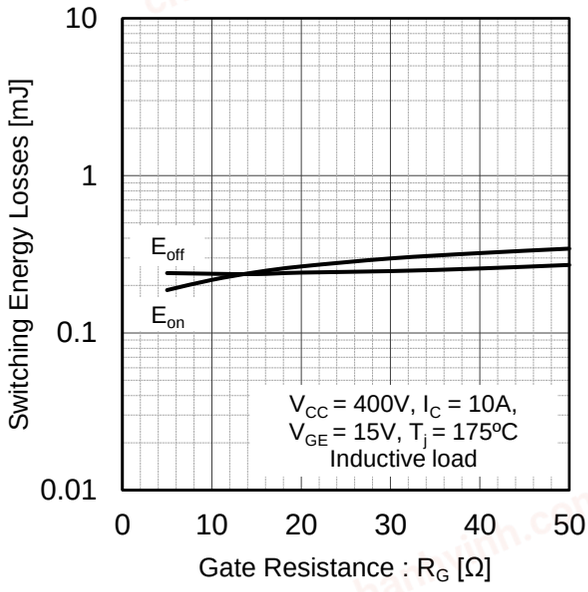


Fig.15 Typical Capacitance vs. Collector to Emitter Voltage

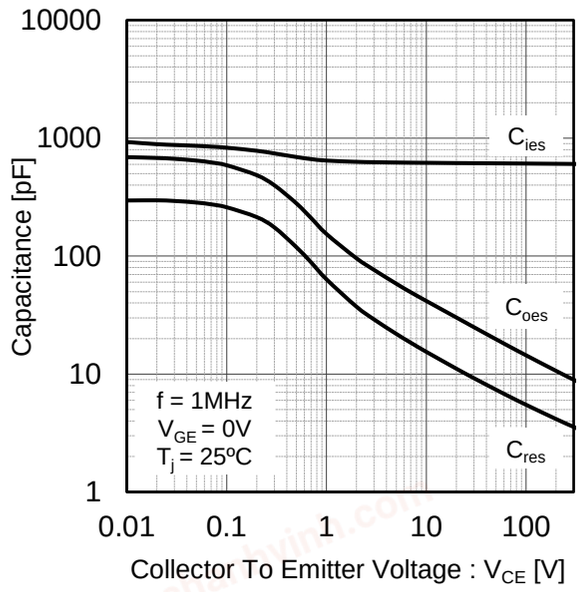
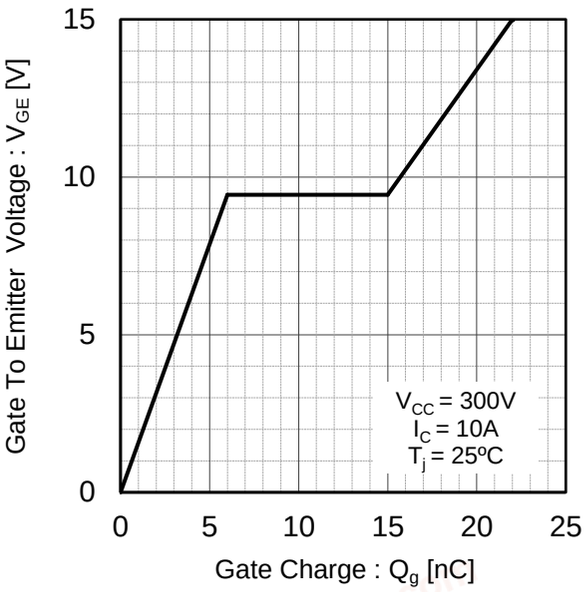


Fig.16 Typical Gate Charge

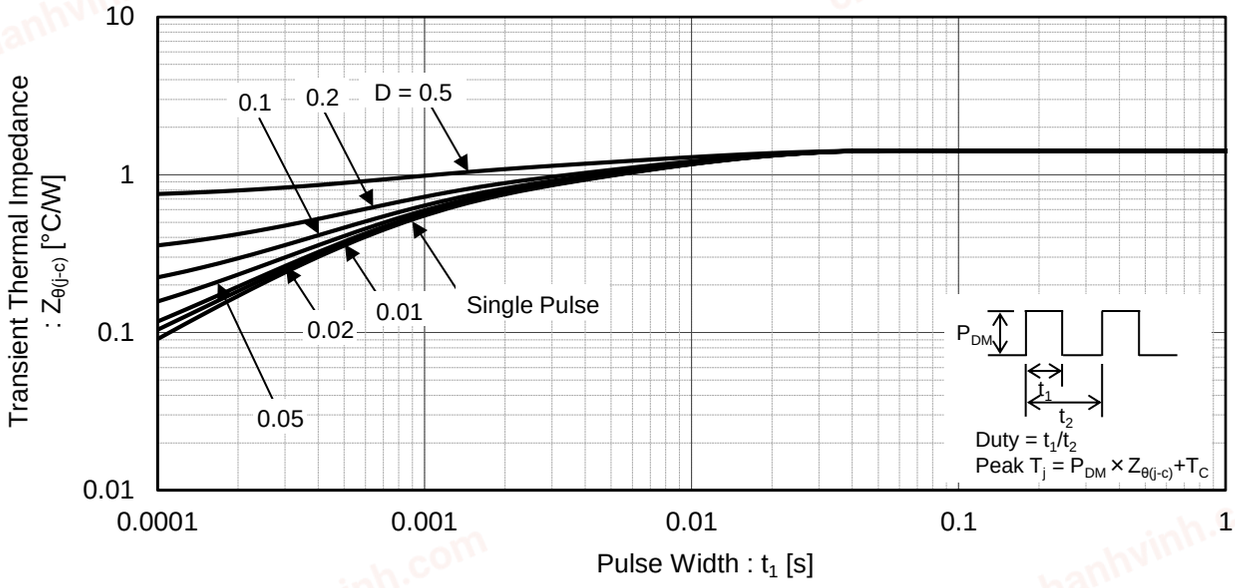


© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

●Inductive Load Switching Circuit and Waveform

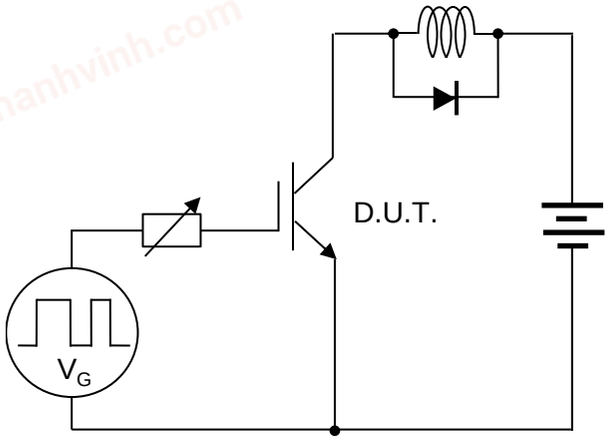


Fig.18 Inductive Load Circuit

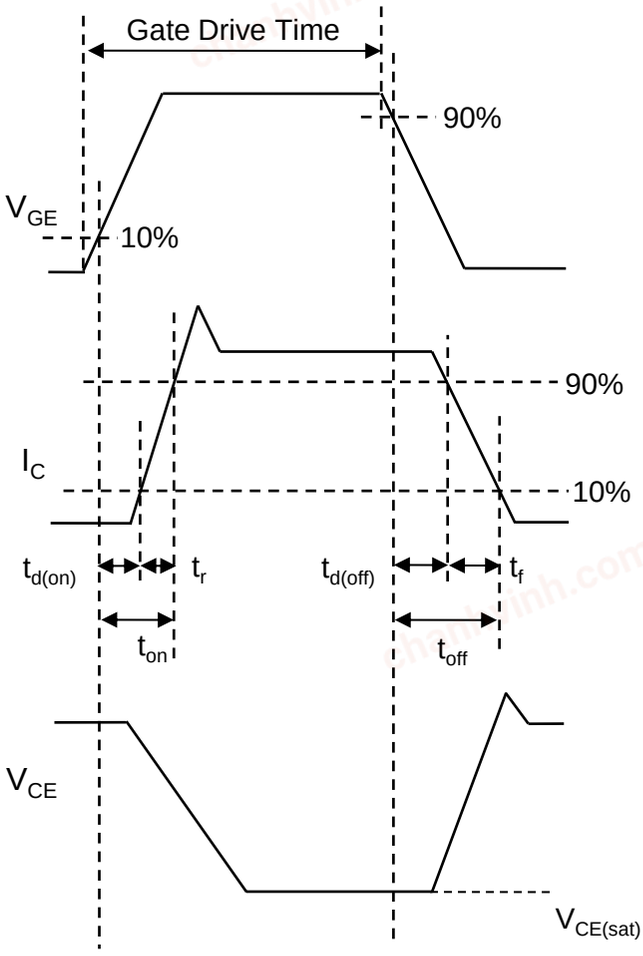


Fig.19 Inductive Load Waveform

© 2019 ROHM Co., Ltd. All rights reserved.

chanhvinh.com

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.

6) The Products specified in this document are not designed to be radiation tolerant.

7) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.

8) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.

9) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.

10) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.

11) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.

12) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.

13) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.

ROHM SEMICONDUCTOR

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

© 2015 ROHM Co., Ltd. All rights reserved.